

TIP145T/146T/147T

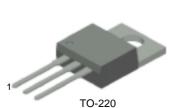
Monolithic Construction With Built In Base-Emitter Shunt Resistors

- High DC Current Gain : h_{FE} = 1000@ V_{CE} = 4V, I_C = 5A (Min.)
- Industrial Use
- Complement to TIP140T/141T/142T

PNP Epitaxial Silicon Darlington Transistor

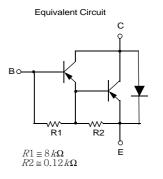
Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage : TIP145T	- 60	V
	: TIP146T	- 80	V
	: TIP147T	- 100	V
	Collector-Emitter Voltage : TIP145T	- 60	V
V _{CEO}	: TIP146T	- 80	V
	: TIP147T	- 100	V
V _{EBO}	Emitter-Base Voltage	- 5	V
I _C	Collector Current (DC)	- 10	А
I _{CP}	Collector Current (Pulse)	- 15	А
I _B	Base Current (DC)	- 0.5	А
P _C	Collector Dissipation (T _C =25°C)	80	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C



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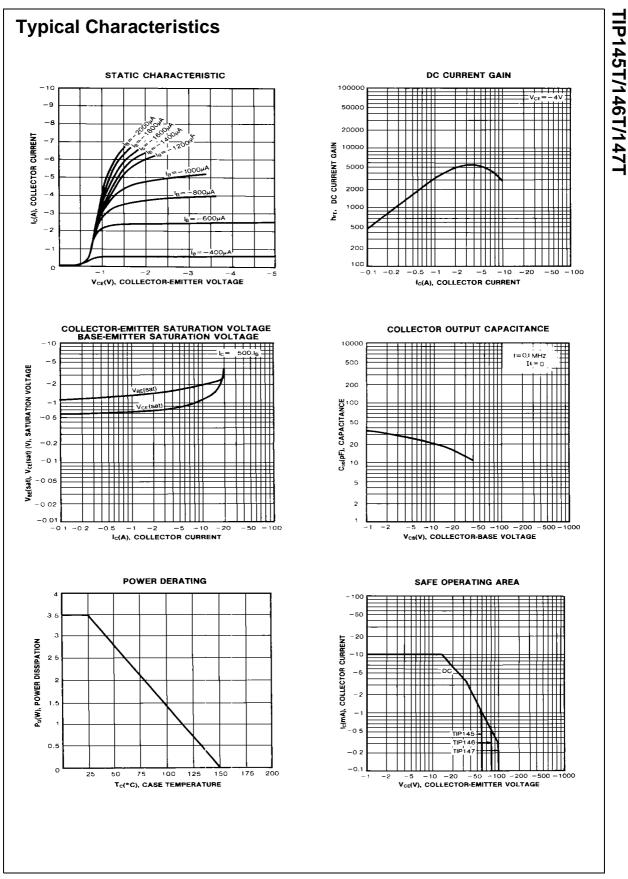
1.Base 2.Collector 3.Emitter



Electrical Characteristics $T_{C}=25^{\circ}C$ unless otherwise noted

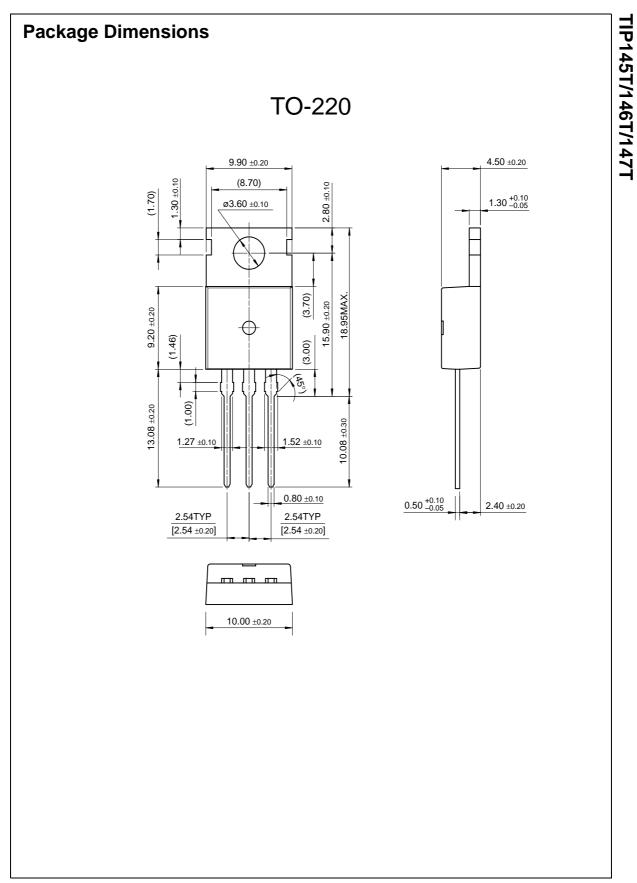
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage : TIP145T : TIP146T : TIP147T	I _C = - 30mA, I _B = 0	- 60 - 80 - 100			V V V
I _{CEO}	Collector Cut-off Current : TIP145T : TIP146T : TIP147T	$V_{CE} = -30V, I_B = 0$ $V_{CE} = -40V, I_B = 0$ $V_{CE} = -50V, I_B = 0$			- 2 - 2 - 2	mA mA mA
I _{CBO}	Collector Cut-off Current : TIP145T : TIP146T : TIP147T	$V_{CB} = -60V, I_E = 0$ $V_{CB} = -80V, I_E = 0$ $V_{CB} = -100V, I_E = 0$			- 1 - 1 - 1	mA mA mA
I _{EBO}	Emitter Cut-off Current	$V_{BE} = -5V, I_{C} = 0$			- 2	mA
h _{FE}	DC Current Gain	$V_{CE} = -4V, I_{C} = -5A$ $V_{CE} = -4V, I_{C} = -10A$	1000 500			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_{C} = -5A, I_{B} = -10mA$ $I_{C} = -10A, I_{B} = -40mA$			- 2 - 3	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = - 10A, I _B = - 40mA			- 3.5	V
V _{BE} (on)	Base-Emitter ON Voltage	V _{CE} = - 4V, I _C = - 10A			- 3	V
t _D	Delay Time	V _{CC} = - 30V, I _C = - 5A		0.15		μs
t _R	Rise Time	$I_{B1} = -20 \text{mA}, I_{B2} = 20 \text{mA}$		0.55		μs
t _{STG}	Storage Time	$R_L = 6\Omega$		2.5		μs
t _F	Fall Time			2.5		μs

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Rev. B, February 2000



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